



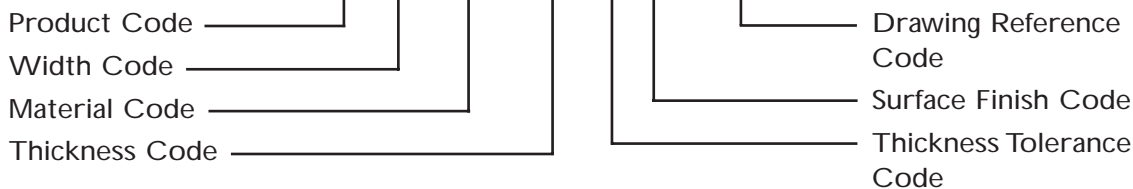
HEAT SINKS AND STANDOFFS

Single Layer Aluminum Nitride for use as Standoffs or Heatsinks.



dielectric laboratories

Part Number



Applications

- Laser diode mounts
- HPA MMIC submounts
- Standoffs

Benefits

- High thermal conductivity
- Low capacitance
- Available with AuSn for solder die attach
- 4.6 PPM/°C coefficient of thermal expansion provides stable match for GaAs and Si die

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Part Number

S 30 AG 250 K Y 1234



Metalization Options

- M= 300Å TiW, 100µ" Au (min)
- T= 300Å TiW, 50µ" Au A side, 300Å TiW, 50µ" NiV, 300µ", AuSn B side
- E= 300Å TiW, 50µ" Au both sides. Patterned TiW/NiV/AuSn (300µ" min) per customer specifications. 4mil minimum exposure of underlying TiW Au to ensure bondability.
- N= 300Å TiW, 50µ" NiV₁/100µ" Au

Characteristics

- Material Aluminum Nitride: >97% purity
- Thermal Conductivity: 170 W/mK
- Coefficient of Thermal Expansion: 4.6 ppm/°C
- Dielectric Constant: 8.85
- Dissipation Factor: .0005 Max @ 1GHz (Unmetalized)
- Insulation Resistance: 10⁶ megohms minimum 25°C

Thickness Code: Thickness in thousandths of an inch.
250 = .025"

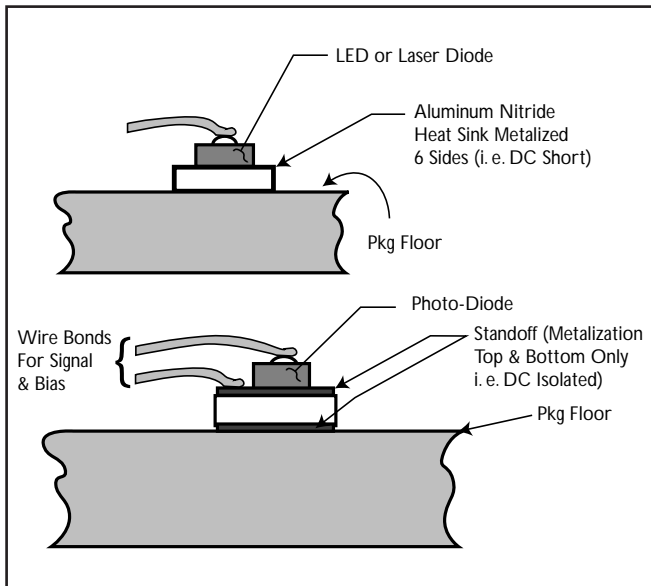
Thickness Tolerance Codes

- K= ± 10% As Fired
- ± .002 Machined

Surface Finish Codes

- X= As Fired
- Y= Machined

Typical Applications



Packaging

Standard: Waffle Packs.
Custom packaging available.
Call with requirements.

Outline Drawing

